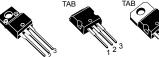


STB100N10F7, STD100N10F7, STF100N10F7 STI100N10F7, STP100N10F7

Datasheet

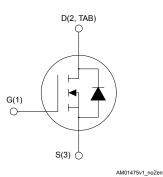
N-channel 100 V, 6.8 m Ω typ., 80 A STripFET F7 Power MOSFETs in D²PAK, DPAK, TO-220FP, I²PAK and TO-220 packages





TO-220

TO-220FP



Features

Order codes	V _{DS}	R _{DS(on)} max.	I _D	Package
STB100N10F7	100 V	100 V 8.0 mΩ	80 A	D ² PAK
STD100N10F7			80 A	DPAK
STF100N10F7			45 A	TO-220FP
STI100N10F7			80 A	I ² PAK
STP100N10F7			80 A	TO-220

• Among the lowest R_{DS(on)} on the market

Excellent FoM (figure of merit)

Low C_{rss}/C_{iss} ratio for EMI immunity

High avalanche ruggedness

Applications

Switching applications

Description

These N-channel Power MOSFETs utilize STripFET F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.



Product status links
STB100N10F7
STD100N10F7
STF100N10F7
STI100N10F7
STP100N10F7



1 Electrical ratings

			Value			
Symbol	Parameter		TO-220FP	D ² PAK I ² PAK TO-220	Unit	
V _{DS}	Drain-source voltage		100		V	
V_{GS}	Gate-source voltage		±20			
1_	Drain current (continuous) at T _C = 25 °C	80	45 ⁽¹⁾	80	Α	
ID	Drain current (continuous) at T _C = 100 °C	62	32 ⁽¹⁾	70	Α	
I _{DM} ⁽²⁾	Drain current (pulsed) 320		180	320	Α	
P _{TOT} ⁽¹⁾	Total power dissipation at T_C = 25 °C	120	30	150	W	
V _{ISO}	Insulation withstand voltage (RMS) from all three leads 2.5 to external heatsink 2.5 (t = 1 s, T _C = 25 °C) 2.5			kV		
TJ	Operating junction temperature		-55 to 175		°C	
T _{stg}	Storage temperature range				°C	

Table 1. Absolute maximum ratings

1. This value is limited by package.

2. Pulse width is limited by safe operating area.

Table 2. Thermal resistance

		Value				
Symbol	nbol Parameter		DPAK	TO-220FP	І ² РАК ТО-220	Unit
R _{thJC}	Thermal resistance, junction-to-case	1	1.25	5	1	°C/W
R _{thJA}	Thermal resistance, junction-to-ambient			62.5		°C/W
R _{thJB} ⁽¹⁾	Thermal resistance, junction-to-board	30	50			°C/W

1. When mounted on an 1-inch² FR-4 board, 2oz CU, t < 10 s.

Table 3. Avalanche characteristics

Symbol	Parameter		Unit
E	Single pulse avalanche energy	400	-
E _{AS}	(T _J = 25 °C, L = 3.5 mH, I _{AS} = 15 A, V _{DD} = 50 V, V _{GS} = 10 V)	400	mJ



2 Electrical characteristics

 T_{CASE} = 25 °C unless otherwise specified.

		Test condi	Test conditions				
Symbol	Parameter	D ² PAK, DPAK I ² PAK, TO-220	TO-220FP	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 250 μA, V _{GS} = 0 V		100			V
	V_{DS} = 100 V, V_{GS} = 0 V				1	μA	
I _{DSS}	Zero gate voltage drain current	V _{DS} = 100 V, V _{GS} = 0 V,				100	
		$T_{\rm C}$ = 125 °C ⁽¹⁾				100	μA
I _{GSS}	Gate-body leakage current	V_{GS} = 20 V, V_{DS} = 0 V	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$		2.5		4.5	V
D Static drain-source on-		V _{GS} = 10 V,	V _{GS} = 10 V,				
R _{DS(on)}	resistance	I _D = 40 A	I _D = 22.5 A		6.8	8.0	mΩ

Table 4. On-/off-states

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C _{iss}	Input capacitance	- V _{DS} = 50 V, f = 1 MHz, - V _{GS} = 0 V		4369	-	pF
C _{oss}	Output capacitance			823	-	pF
C _{rss}	Reverse transfer capacitance			36	-	pF
Qg	Total gate charge	V _{DD} = 50 V, I _D = 80 A,	-	61	-	nC
Q _{gs}	Gate-source charge	V _{GS} = 0 to 10 V	-	26	-	nC
Q _{gd}	Gate-drain charge	(see Figure 17. Test circuit for gate charge behavior)	-	13	-	nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)}	Turn-on delay time	V _{DD} = 50 V, I _D = 40 A,	-	27	-	ns
tr	Rise time	R_{G} = 4.7 Ω , V_{GS} = 10 V	-	40	-	ns
t _{d(off)}	Turn-off delay time	(see Figure 16. Test circuit for resistive load switching times and Figure 21. Switching time		46	-	ns
t _f	Fall time	waveform)	-	15	-	ns

Table 7. Source-drain diode

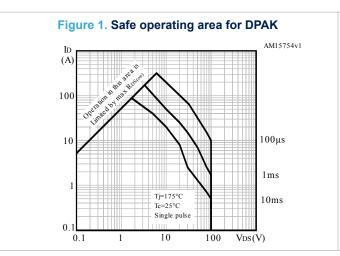
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SD}	Source-drain current		-		80	A
I _{SDM} ⁽¹⁾	Source-drain current (pulsed)		-		320	А
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} = 80 A, V _{GS} = 0 V	-		1.2	V
t _{rr}	Reverse recovery time	I _{SD} = 80 A, di/dt = 100 A/μs	-	77		ns
Q _{rr}	Reverse recovery charge	V _{DD} = 80 V, T _J = 150 °C	-	146		nC
I _{RRM}	Reverse recovery current	(see Figure 18. Test circuit for inductive load switching and diode recovery times)	-	4		А

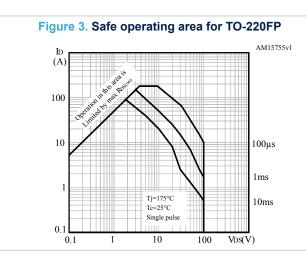
1. Pulse width is limited by safe operating area.

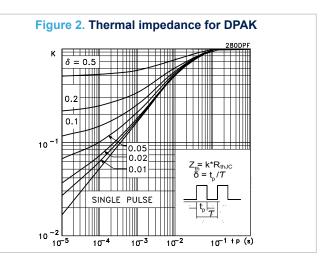
2. Pulsed: pulse duration = $300 \ \mu$ s, duty cycle 1.5%

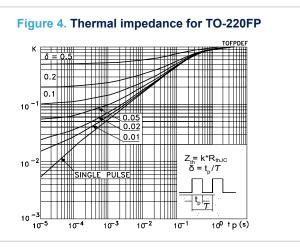


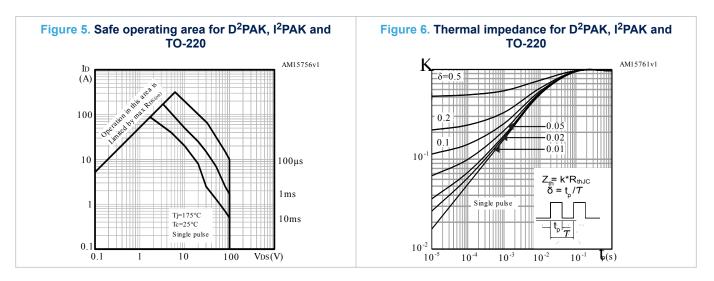
2.1 Electrical characteristics (curves)







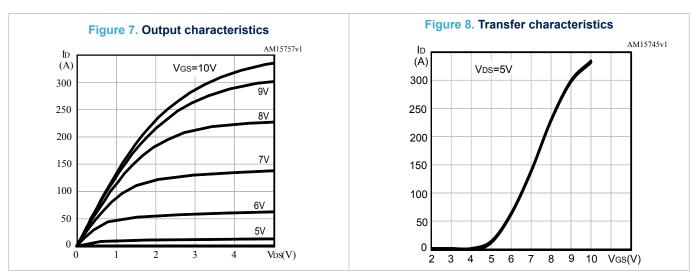


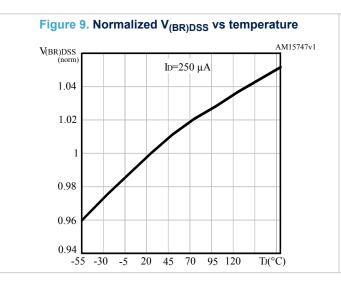


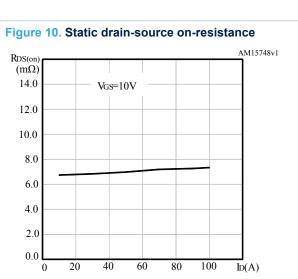
DS9291 - Rev 6	
d from Arrow com	

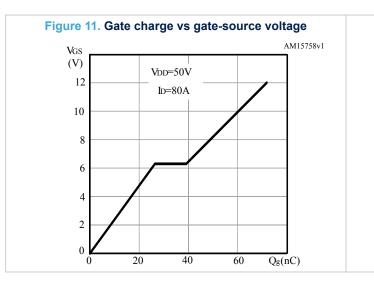
Downloade



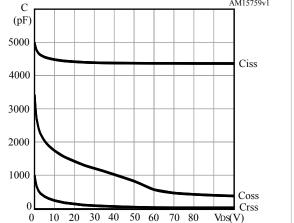




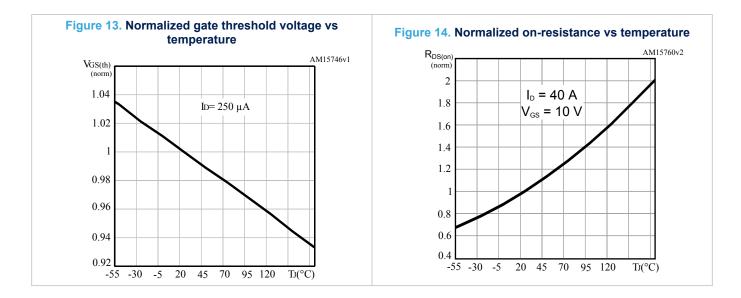


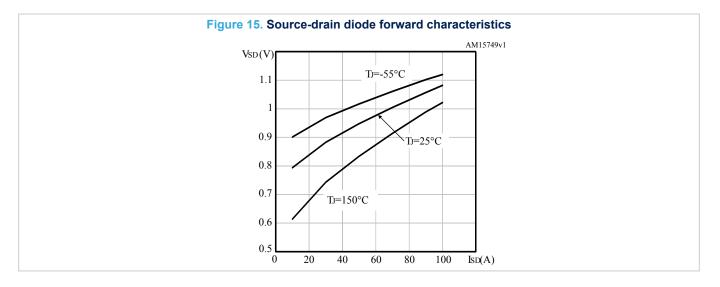






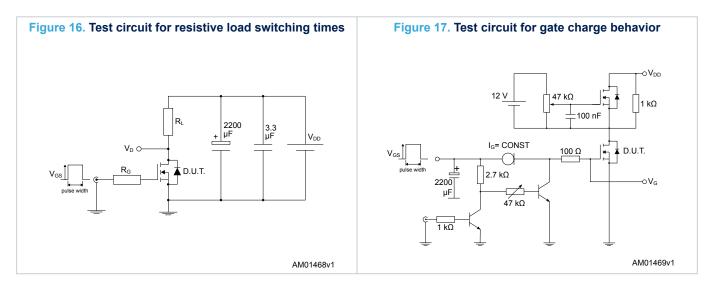


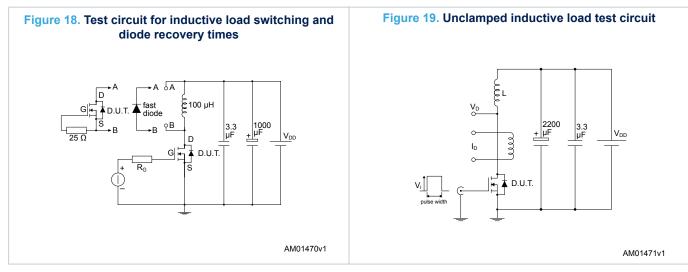


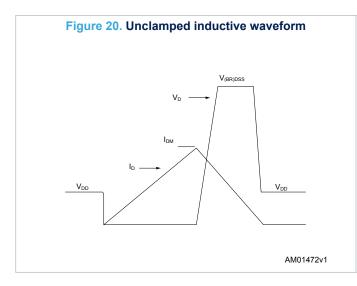


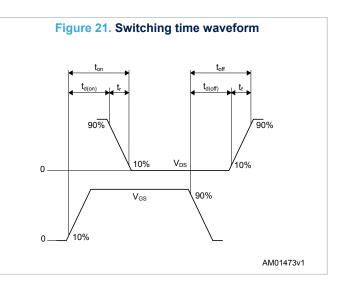


3 Test circuits









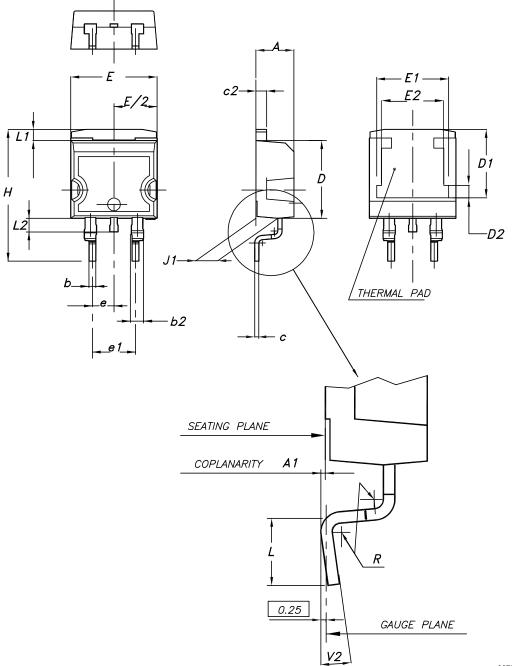


4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 D²PAK (TO-263) type A package information

Figure 22. D²PAK (TO-263) type A package outline

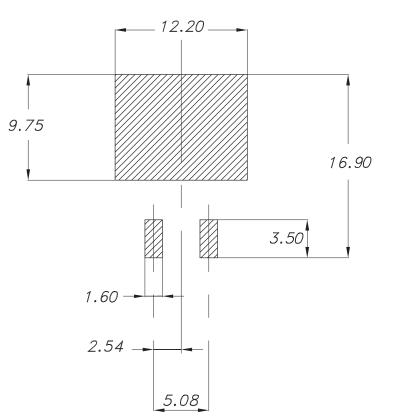


0079457_26



Dim.	mm					
Dim.	Min.	Тур.	Max.			
А	4.40		4.60			
A1	0.03		0.23			
b	0.70		0.93			
b2	1.14		1.70			
С	0.45		0.60			
c2	1.23		1.36			
D	8.95		9.35			
D1	7.50	7.75	8.00			
D2	1.10	1.30	1.50			
E	10.00		10.40			
E1	8.30	8.50	8.70			
E2	6.85	7.05	7.25			
е		2.54				
e1	4.88		5.28			
Н	15.00		15.85			
J1	2.49		2.69			
L	2.29		2.79			
L1	1.27		1.40			
L2	1.30		1.75			
R		0.40				
V2	0°		8°			

Table 8. D²PAK (TO-263) type A package mechanical data



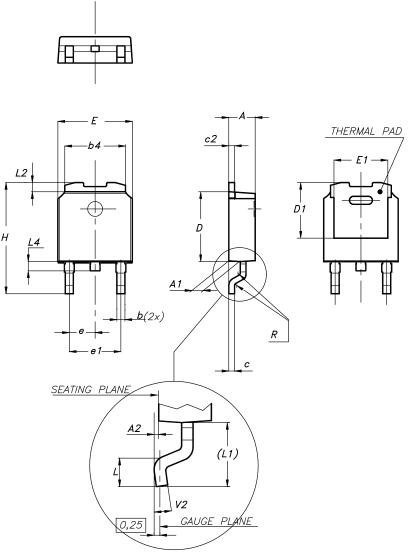


0079457_Rev26_footprint



4.2 DPAK (TO-252) type A2 package information

Figure 24. DPAK (TO-252) type A2 package outline



0068772_type-A2_rev30



Dim.		mm	
Dim.	Min.	Тур.	Max.
А	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
С	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
Н	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

Table 9. DPAK (TO-252) type A2 mechanical data



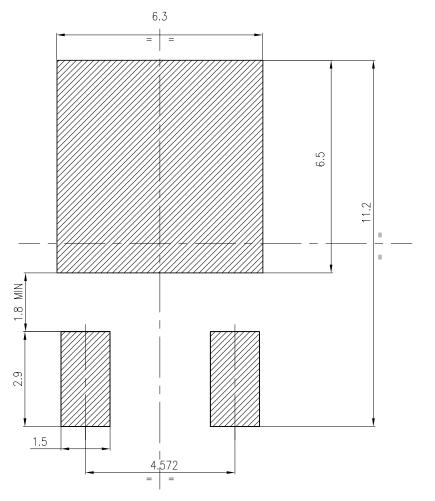


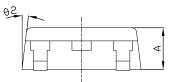
Figure 25. DPAK (TO-252) recommended footprint (dimensions are in mm)

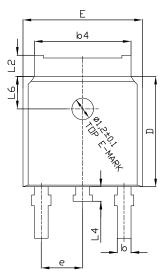
FP_0068772_30

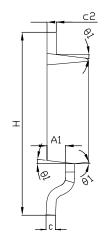


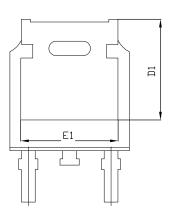
4.3 DPAK (TO-252) type C package information

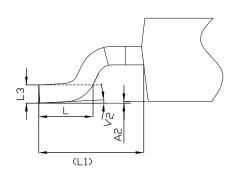
Figure 26. DPAK (TO-252) type C package outline











0068772_C_30



Dim.	mm			
Dim.	Min.	Тур.	Max.	
A	2.20	2.30	2.38	
A1	0.90	1.01	1.10	
A2	0.00		0.10	
b	0.72		0.85	
b4	5.13	5.33	5.46	
C	0.47		0.60	
c2	0.47		0.60	
D	6.00	6.10	6.20	
D1	5.25			
E	6.50	6.60	6.70	
E1	4.70			
е	2.186	2.286	2.386	
Н	9.80	10.10	10.40	
L	1.40	1.50	1.70	
L1		2.90 REF	·	
L2	0.90		1.25	
L3		0.51 BSC	·	
L4	0.60	0.80	1.00	
L6		1.80 BSC		
θ1	5°	7°	9°	
θ2	5°	7°	9°	
V2	0°		8°	

Table 10. DPAK (TO-252) type C mechanical data



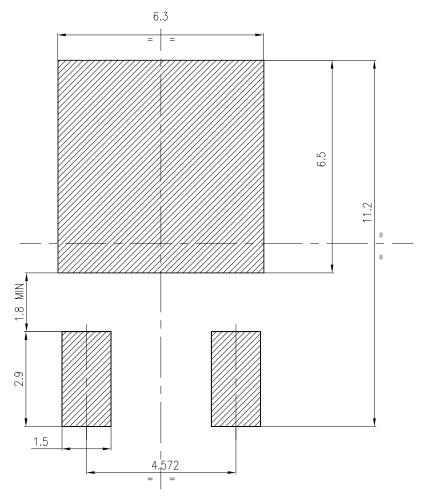


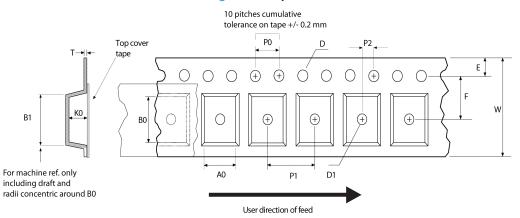
Figure 27. DPAK (TO-252) recommended footprint (dimensions are in mm)

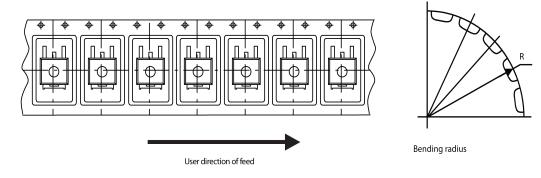
FP_0068772_30



4.4 D²PAK and DPAK packing information

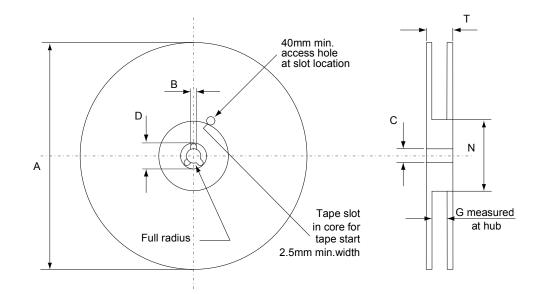
Figure 28. Tape outline





AM08852v1

Figure 29. Reel outline



AM06038v1

Таре		Reel			
Dim.	mm		Dim	mm	
Dim.	Min.	Max.	Dim.	Min.	Max.
A0	10.5	10.7	А		330
B0	15.7	15.9	В	1.5	
D	1.5	1.6	С	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
К0	4.8	5.0	Т		30.4
P0	3.9	4.1		·	
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
Т	0.25	0.35			
W	23.7	24.3			

Table 11. D²PAK tape and reel mechanical data



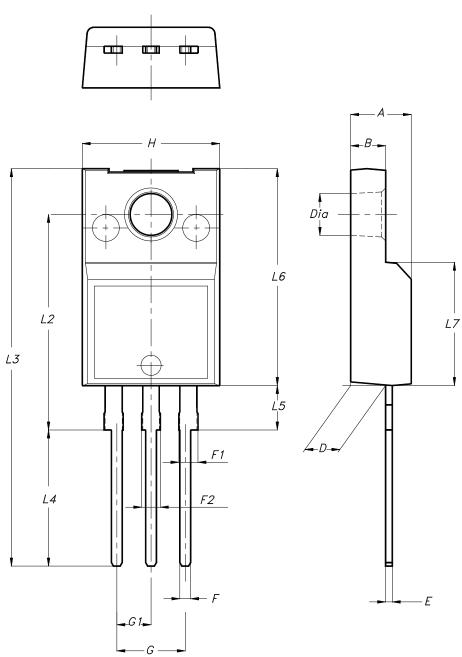
Таре			Reel		
Dim.	m	mm		mm	
	Min.	Max.	– Dim.	Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	В	1.5	
B1		12.1	С	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	Т		22.4
K0	2.55	2.75			
P0	3.9	4.1	Bas	e qty.	2500
P1	7.9	8.1	Bul	k qty.	2500
P2	1.9	2.1			
R	40				
Т	0.25	0.35			
W	15.7	16.3			

Table 12. DPAK tape and reel mechanical data



4.5 TO-220FP package information

Figure 30. TO-220FP package outline



7012510_Rev_13_B



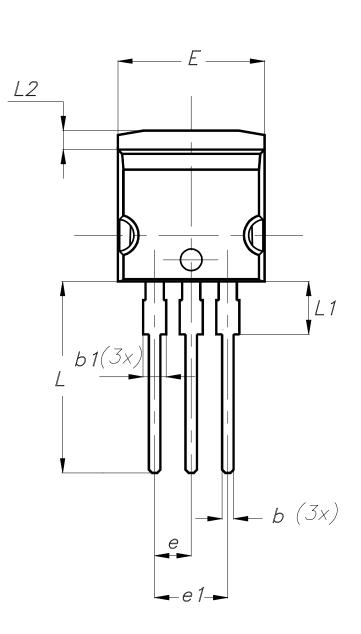
Dim.	mm			
	Min.	Тур.	Max.	
А	4.40		4.60	
В	2.50		2.70	
D	2.50		2.75	
E	0.45		0.70	
F	0.75		1.00	
F1	1.15		1.70	
F2	1.15		1.70	
G	4.95		5.20	
G1	2.40		2.70	
Н	10.00		10.40	
L2		16.00		
L3	28.60		30.60	
L4	9.80		10.60	
L5	2.90		3.60	
L6	15.90		16.40	
L7	9.00		9.30	
Dia	3.00		3.20	

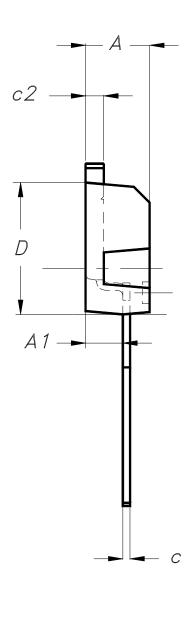
Table 13. TO-220FP package mechanical data



4.6 I²PAK package information

Figure 31. I²PAK package outline





0004982_Rev_9



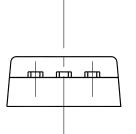
Dim.	mm			
Dim.	Min.	Тур.	Max.	
A	4.40	-	4.60	
A1	2.40	-	2.72	
b	0.61	-	0.88	
b1	1.14	-	1.70	
С	0.49	-	0.70	
c2	1.23	-	1.32	
D	8.95	-	9.35	
e	2.40	-	2.70	
e1	4.95	-	5.15	
E	10.00	-	10.40	
L	13.00	-	14.00	
L1	3.50	-	3.93	
L2	1.27	-	1.40	

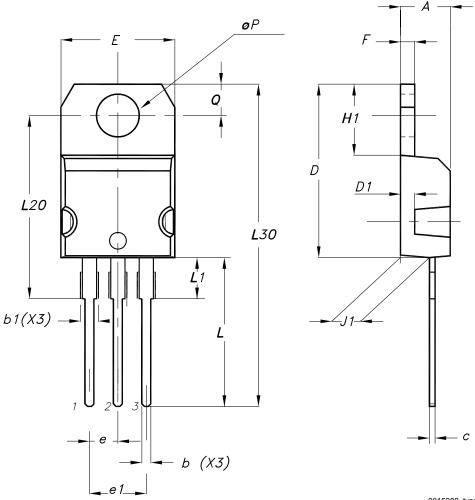
Table 14. I²PAK package mechanical data



4.7 TO-220 type A package information

Figure 32. TO-220 type A package outline





0015988_typeA_Rev_23



Dim.	mm			
	Min.	Тур.	Max.	
A	4.40		4.60	
b	0.61		0.88	
b1	1.14		1.55	
C	0.48		0.70	
D	15.25		15.75	
D1		1.27		
E	10.00		10.40	
e	2.40		2.70	
e1	4.95		5.15	
F	1.23		1.32	
H1	6.20		6.60	
J1	2.40		2.72	
L	13.00		14.00	
L1	3.50		3.93	
L20		16.40		
L30		28.90		
øP	3.75		3.85	
Q	2.65		2.95	
Slug flatness		0.03	0.10	

Table 15. TO-220 type A package mechanical data



5 Ordering information

Table 16. Order codes

Order code	Marking	Package	Packing
STB100N10F7	100N10F7	D ² PAK	Tape and reel
STD100N10F7		DPAK	Tape and reel
STF100N10F7		TO-220FP	Tube
STI100N10F7		I ² PAK	Tube
STP100N10F7		TO-220	Tube



Revision history

Date	Version	Changes
05-Oct-2012	1	Initial release.
		Inserted device in TO-220FP.
07-Feb-2013	2	Updated title and features on the cover page, <i>Table 1: Device summary, Table 2: Absolute maximum ratings, Table 3: Thermal resistance</i> and <i>Table 5: On/off states</i> accordingly.
		Updated Table 6: Dynamic, Table 7: Switching times, Table 8: Source drain diode and Section 4: Package mechanical data.
		Added Section 5: Packaging mechanical data.
		Modified: the entire typical values in <i>Table 6</i> , tf typical value in <i>Table 7</i> , VSD and typical values for trr, qrr, IRRM
29-Apr-2013	3	Inserted: Table 4: Avalanche characteristics and Section 2.1: Electrical characteristics (curves)
		Minor text changes
		Inserted device in D ² PAK.
25-Nov-2013	4	Updated title and features on the cover page, <i>Table 1: Device summary, Table 2: Absolute maximum ratings, Table 3: Thermal resistance</i> and <i>Table 5: On/off states</i> accordingly.
		Updated Table 6: Dynamic, Section 4: Package mechanical data and Section 5: Packaging mechanical data.
		Added STI100N10F7 device and updated the document accordingly.
		Removed maturity status indication, updated title, features and description on
18-Jun-2018	5	cover page.
		Updated Table 1. Absolute maximum ratings.
		Updated Section 4 Package information.
		Minor text changes.
02-Mar-2022	6	Updated Section 4 Package information.
	•	Minor text changes.

Table 17. Document revision history



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1	Elect	rical ratings	2				
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3	Test	circuits	8				
4	Pack	age information	9				
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	4.2	DPAK (TO-252) type A2 package information	. 12				
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